TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC3328

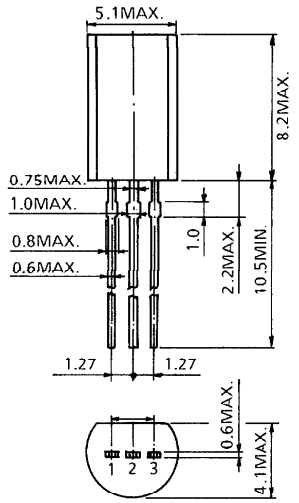
POWER AMPLIFIER APPLICATIONS.

POWER SWITCHING APPLICATIONS.

INDUSTRIAL APPLICATIONS

- Low Saturation Voltage
  : $V_{CE\,(sat)}$ = 0.5V (Max.) (I_C = 1A)
- High Speed Switching Time : t_{stg} = 1.0 μs (Typ.)
- Complementary to 2SA1315

Unit in mm



1. EMITTER
2. COLLECTOR
3. BASE

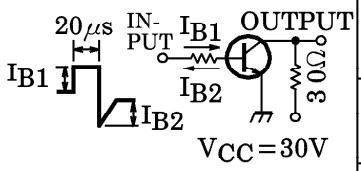
JEDEC	TO-92MOD
EIAJ	—
TOSHIBA	2-5J1A

Weight : 0.36g

MAXIMUM RATINGS (Ta = 25°C)

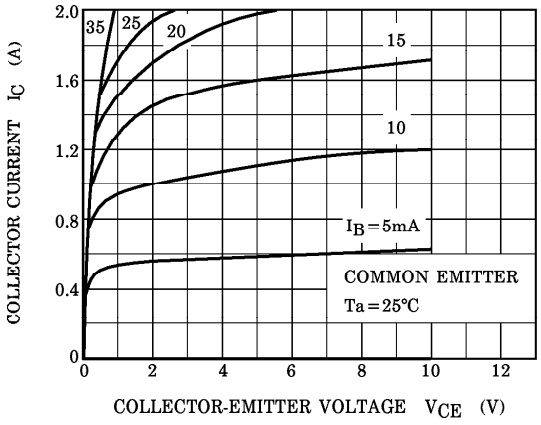
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	2	A
Base Current	I_B	1	A
Collector Power Dissipation	P_C	900	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

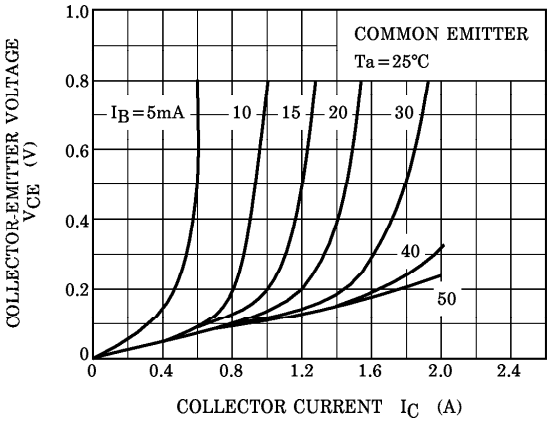
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	V_{CB} = 80V, I_E = 0	—	—	1.0	μA
Emitter Cut-off Current		I_{EBO}	V_{EB} = 5V, I_C = 0	—	—	1.0	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	I_C = 10mA, I_B = 0	80	—	—	V
DC Current Gain		$h_{FE(1)}$ (Note)	V_{CE} = 2V, I_C = 0.5A	70	—	240	
		$h_{FE(2)}$	V_{CE} = 2V, I_C = 1.5A	40	—	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C = 1A, I_B = 0.05A	—	0.15	0.5	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	I_C = 1A, I_B = 0.05A	—	0.9	1.2	V
Transition Frequency		f_T	V_{CE} = 2V, I_C = 0.5A	—	100	—	MHz
Collector Output Capacitance		C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	—	30	—	pF
Switching Time	Turn-on Time	t_{on}		—	0.2	—	μs
	Storage Time	t_{stg}		—	1.0	—	
	Fall Time	t_f	$I_{B1} = -I_{B2} = 0.05A$, DUTY CYCLE ≦ 1%	—	0.2	—	

Note : $h_{FE(1)}$ Classification O : 70~140, Y : 120~240

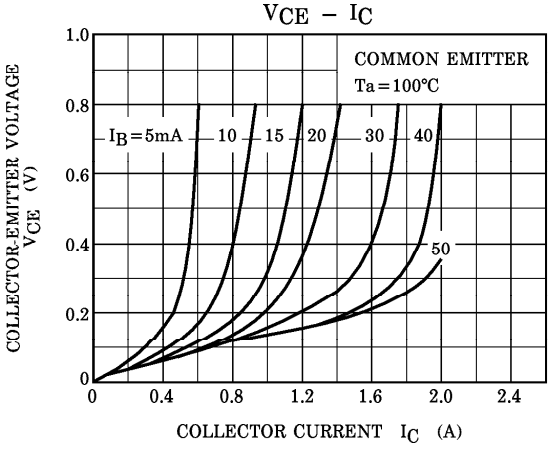
I_C – V_{CE}



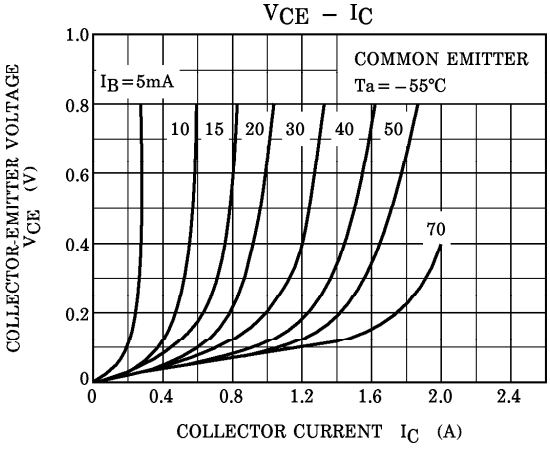
V_{CE} – I_C



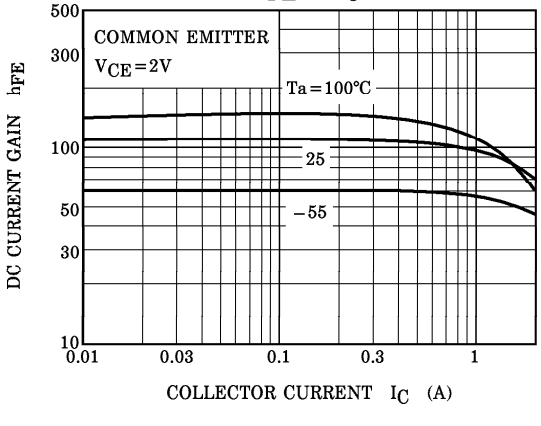
V_{CE} – I_C



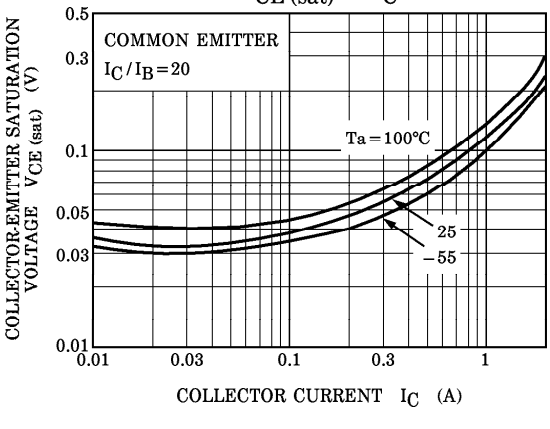
V_{CE} – I_C



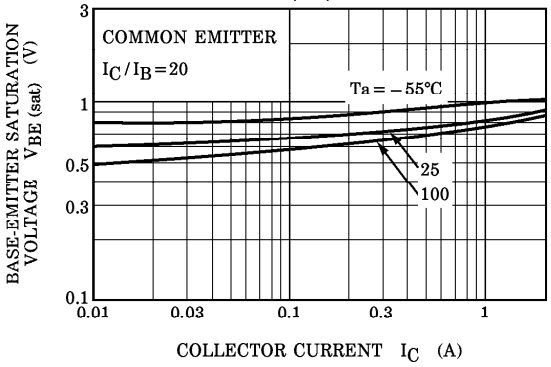
h_{FE} – I_C



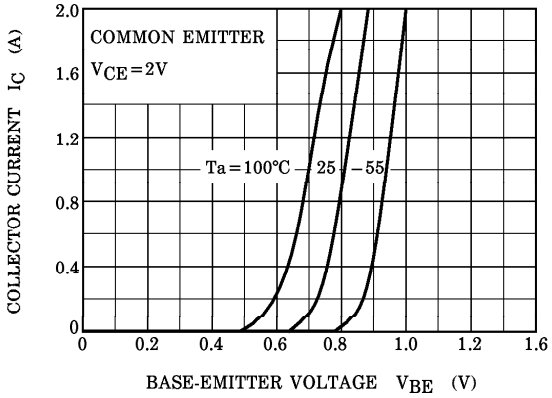
$V_{CE\,(sat)}$ – I_C



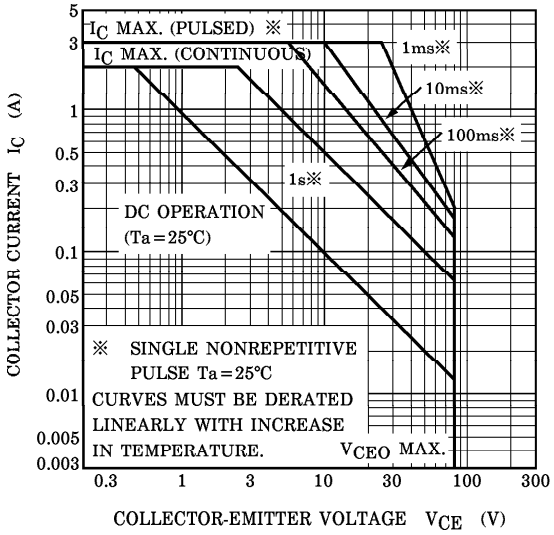
$V_{BE\,(sat)}$ – I_C



I_C – V_{BE}



SAFE OPERATING AREA



P_C – Ta